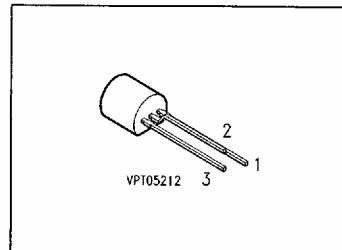


NPN Silicon RF Transistors

BF 254
BF 255

- For AM and FM stages



Type	Marking	Ordering Code	Pin Configuration			Package ¹⁾
			1	2	3	
BF 254	–	Q62702-F201	C	E	B	TO-92
BF 255		Q62702-F202				

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CEO}	20	V
Collector-base voltage	V_{CES}	30	
Emitter-base voltage	V_{EBO}	5	
Collector current	I_C	30	mA
Total power dissipation, $T_A \leq 45^\circ\text{C}$	P_{tot}	250	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	– 65 ... + 150	

Thermal Resistance

Junction - ambient	$R_{th JA}$	≤ 420	K/W
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¹⁾ For detailed information see chapter Package Outlines.

Electrical Characteristics

at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

DC current gain $I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}$ BF 254 BF 255	h_{FE}				-
		65	-	220	
		35	-	130	
Base-emitter voltage $I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}$	V_{BE}	-	0.68	-	V

AC Characteristics

Transition frequency $I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}, f = 100 \text{ MHz}$ BF 254 BF 255	f_T				MHz
		-	260	-	
		-	220	-	
Collector-base capacitance $V_{CB} = 10 \text{ V}, V_{BE} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{cb}	-	0.6	-	pF
Collector-emitter capacitance $V_{CE} = 10 \text{ V}, V_{BE} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{ce}	-	0.6	-	
Noise figure $I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}$ $f = 1 \text{ MHz}, g_s = 1.5 \text{ mS}^1)$ $f = 100 \text{ MHz}, g_s = 10 \text{ mS}^1)$	F				dB
		-	1.2	-	
		-	3.8	-	

Y parameters, typical values, $I_C = 10 \text{ V}$

f MHz		g_{11} mS	b_{11} mS	$ y_{12} $ μS	ϕ_{12} deg.	$ y_{21} $ mS	ϕ_{21} deg.	g_{22} μS	b_{22} μS
Common emitter									
0.45	BF 254	0.3	0.06	1.7	-90	38	0	3.2	3.4
	BF 255	0.45	0.08	1.7	-90	38	0	2.7	3.4
10.7	BF 254	0.4	1.5	41	-90	37	-10	4	8.1
	BF 255	0.5	1.75	41	-90	37	-10	3.8	8.1
Common base									
100	BF 255	34	-3.5	250	-85	33	150	18	700

¹⁾ $g_s = \text{generator conductance}$

Total power dissipation $P_{\text{tot}} = f(T_A)$

